

### THYRISTOR / DIODE and THYRISTOR / THYRISTOR

### SUPER MAGN-A-pak™ Power Modules

#### Features

- High current capability
- 3000 V<sub>RMS</sub> isolating voltage with non-toxic substrate
- High surge capability
- High voltage ratings up to 2000V
- Industrial standard package
- UL recognition pending

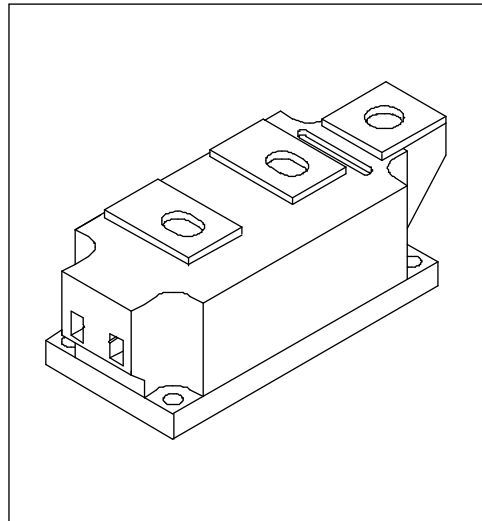
430 A

#### Typical Applications

- Motor starters
- DC motor controls - AC motor controls
- Uninterruptable power supplies
- Wind mill

#### Major Ratings and Characteristics

Parameters	IRK.430..	Units
$I_{T(AV)}$ or $I_{F(AV)}$	430	A
@ $T_C$	82	°C
$I_{T(RMS)}$	675	A
@ $T_C$	82	°C
$I_{TSM}$ or $I_{FSM}$	15.7	KA
@ 50Hz		
@ 60Hz	16.4	KA
$I^2t$	1232	KA <sup>2</sup> s
@ 50Hz		
@ 60Hz	1125	KA <sup>2</sup> s
$I^2\sqrt{t}$	12320	KA <sup>2</sup> √s
$V_{DRM}/V_{RRM}$ range	1600 to 2000	V
$T_{STG}$ range	-40 to 150	°C
$T_J$ range	-40 to 130	°C



**ELECTRICAL SPECIFICATIONS**

**Voltage Ratings**

Type number	Voltage Code	$V_{RRM}/V_{DRM}$ maximum repetitive peak reverse voltage V	$V_{RSM}$ , maximum non-repetitive peak rev. voltage V	$I_{RRM}/I_{DRM}$ max. @ $T_J = T_J$ max. mA
IRK.430..	16	1600	1700	100
	18	1800	1900	
	20	2000	2100	

**On-state Conduction**

Parameter	IRK.430..	Units	Conditions
$I_{T(AV)}$ Maximum average on-state current @ Case temperature	430	A	180° conduction, half sine wave
$I_{F(AV)}$	82	°C	
$I_{T(RMS)}$ Maximum RMS on-state current	675	A	180° conduction, half sine wave @ $T_C = 82^\circ\text{C}$
$I_{TSM}$ Maximum peak, one-cycle, non-repetitive surge current $I_{FSM}$	15.7	KA	t = 10ms No voltage
	16.4		t = 8.3ms reappplied
	13.2		t = 10ms 100% $V_{RRM}$
	13.8		t = 8.3ms reappplied
$I^2t$ Maximum $I^2t$ for fusing	1232	KA <sup>2</sup> s	t = 10ms No voltage
	1125		t = 8.3ms reappplied
	871		t = 10ms 100% $V_{RRM}$
	795		t = 8.3ms reappplied
$I^2/t$ Maximum $I^2/t$ for fusing	12320	KA <sup>2</sup> /s	t = 0.1 to 10ms, no voltage reappplied
$V_{T(TO)1}$ Low level value of threshold voltage	0.96	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ max.
$V_{T(TO)2}$ High level value of threshold voltage	1.06		$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ max.
$r_{t1}$ Low level value of on-state slope resistance	0.51	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ max.
$r_{t2}$ High level value of on-state slope resistance	0.45		$(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ max.
$V_{TM}$ Maximum on-state or forward voltage drop $V_{FM}$	1.65	V	$I_{pk} = 1500A$ , $T_J = 25^\circ\text{C}$ , $t_p = 10\text{ms}$ sine pulse
$I_H$ Maximum holding current	500	mA	$T_J = 25^\circ\text{C}$ , anode supply 12V resistive load
$I_L$ Typical latching current	1000		

**Switching**

Parameter	IRK.430..	Units	Conditions
di/dt Maximum rate of rise of turned-on current	1000	A/μs	$T_J = T_J$ max., $I_{TM} = 400A$ , $V_{DRM}$ applied
$t_d$ Typical delay time	2.0	μs	Gate current 1A, $di_g/dt = 1A/\mu\text{s}$ $V_d = 0.67\% V_{DRM}$ , $T_J = 25^\circ\text{C}$
$t_q$ Typical turn-off time	200	μs	$I_{TM} = 750A$ , $T_J = T_J$ max, $di/dt = -60A/\mu\text{s}$ , $V_R = 50V$ , $dv/dt = 20V/\mu\text{s}$ , Gate 0 V 100Ω

### Blocking

Parameter	IRK.430..	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	1000	V/ $\mu$ s	$T_J = 130^\circ\text{C}$ ., linear to $V_D = 80\% V_{DRM}$
$V_{INS}$ RMS isolation voltage	3000	V	$t = 1 \text{ s}$
$I_{RRM}$ Maximum peak reverse and off-state leakage current $I_{DRM}$	100	mA	$T_J = T_J \text{ max.}$ ., rated $V_{DRM}/V_{RRM}$ applied

### Triggering

Parameter	IRK.430..	Units	Conditions
$P_{GM}$ Maximum peak gate power	10	W	$T_J = T_J \text{ max.}$ ., $t_p \leq 5\text{ms}$
$P_{G(AV)}$ Maximum peak average gate power	2.0	W	$T_J = T_J \text{ max.}$ ., $f = 50\text{Hz}$ , $d\% = 50$
$+I_{GM}$ Maximum peak positive gate current	3.0	A	$T_J = T_J \text{ max.}$ ., $t_p \leq 5\text{ms}$
$+V_{GM}$ Maximum peak positive gate voltage	20	V	
$-V_{GM}$ Maximum peak negative gate voltage	5.0	V	
$I_{GT}$ Max. DC gate current required to trigger	200	mA	$T_J = 25^\circ\text{C}$ $V_{ak} 12\text{V}$
$V_{GT}$ DC gate voltage required to trigger	3.0	V	$T_J = 25^\circ\text{C}$ $V_{ak} 12\text{V}$
$I_{GD}$ DC gate current not to trigger	10	mA	$T_J = T_J \text{ max.}$
$V_{GD}$ DC gate voltage not to trigger	0.25	V	

### Thermal and Mechanical Specifications

Parameter	IRK.430..	Units	Conditions
$T_J$ Max. junction operating temperature range	- 40 to 130	°C	
$T_{stg}$ Max. storage temperature range	- 40 to 150		
$R_{thJC}$ Max. thermal resistance, junction to case	0.065	K/W	Per junction, DC operation
$R_{thC-hs}$ Max. thermal resistance, case to heatsink	0.02	K/W	
T Mounting torque $\pm 10\%$ SMAP to heatsink busbar to SMAP	6 - 8	Nm	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound
	12 - 15		
wt Approximate weight	1500	g	
Case style	SUPER MAGN-A-pak		See outline table

## IRK.430.. Series

Bulletin I27400 rev. A 09/97

International  
**IRF** Rectifier

### $\Delta R_{thJC}$ Conduction

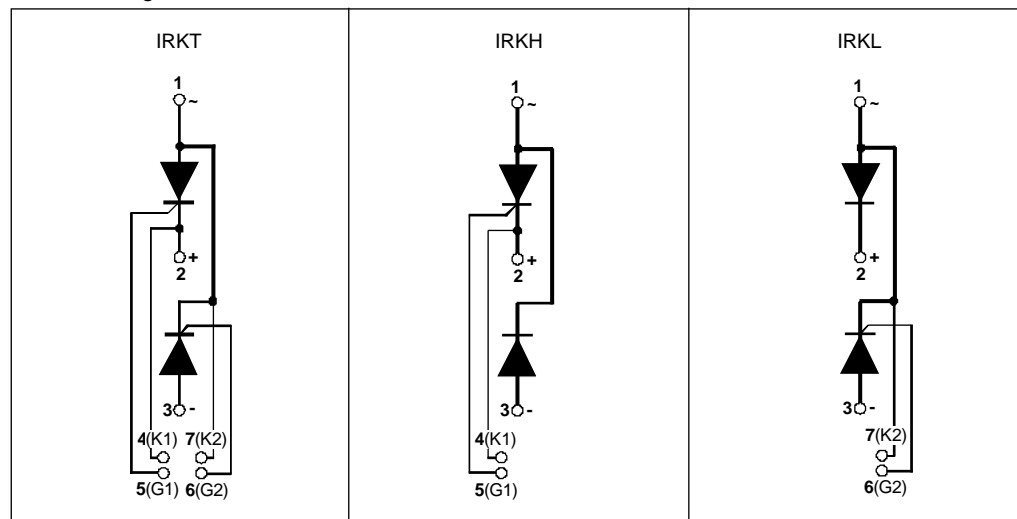
(The following table shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction	Rectangular conduction	Units	Conditions
180°	0.009	0.006	K/W	$T_J = T_{J \text{ max.}}$
120°	0.011	0.011		
90°	0.014	0.015		
60°	0.021	0.022		
30°	0.037	0.038		

### Ordering Information Table

Device Code				
1	2	3	4	5
IRK	T	430	-	20
<b>1</b> - Module type	<b>2</b> - Circuit configuration (See Circuit Configurations Table)	<b>3</b> - Current rating	<b>4</b> - Voltage code: Code x 100 = $V_{RRM}$ (See Voltage Ratings Table)	

### Circuit Configurations Table



**NOTE: To order the Optional Hardware see Bulletin I27900**

Outline Table

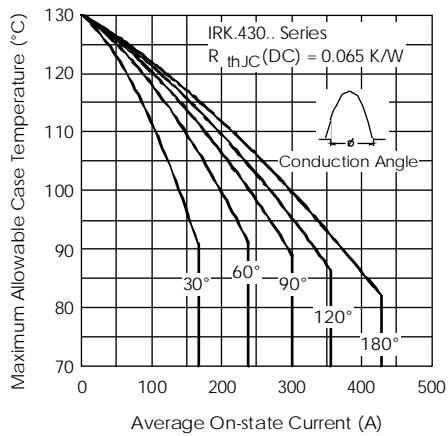
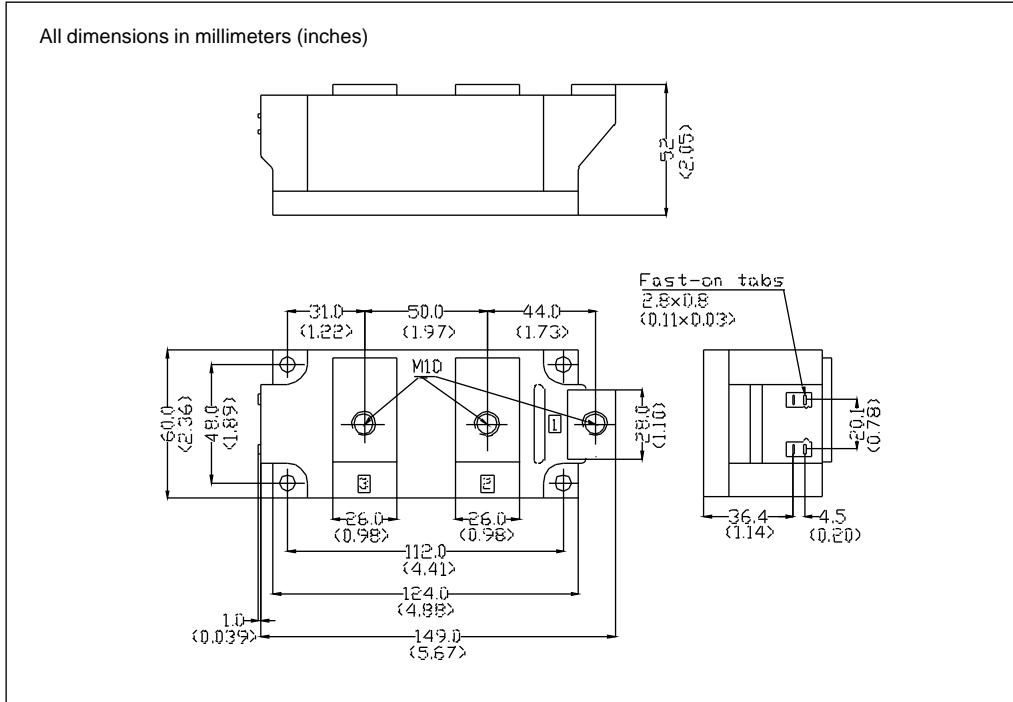


Fig. 1 - Current Ratings Characteristics

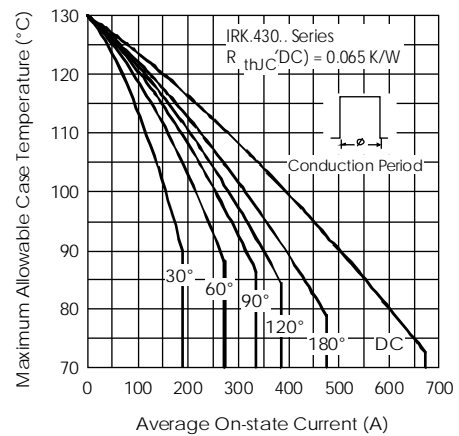


Fig. 2 - Current Ratings Characteristics

# IRK.430.. Series

Bulletin I27400 rev. A 09/97

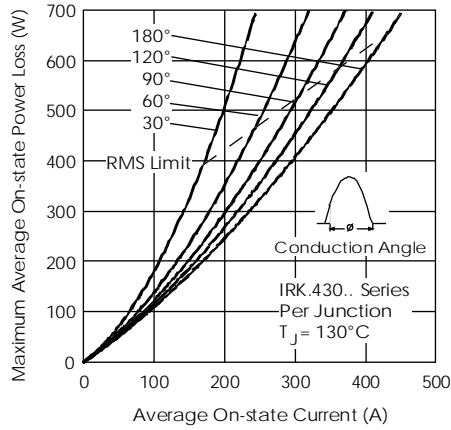


Fig. 3 - On-state Power Loss Characteristics

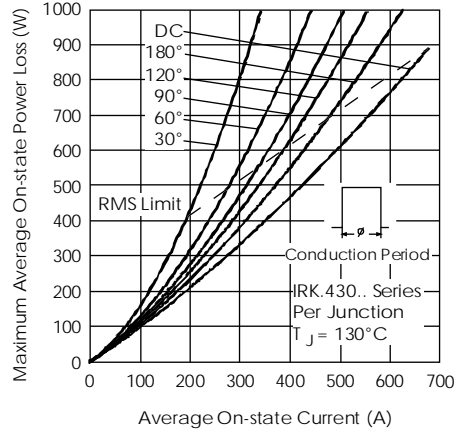


Fig. 4 - On-state Power Loss Characteristics

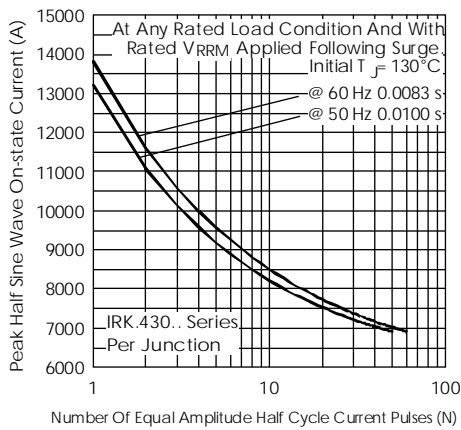


Fig. 5 - Maximum Non-Repetitive Surge Current

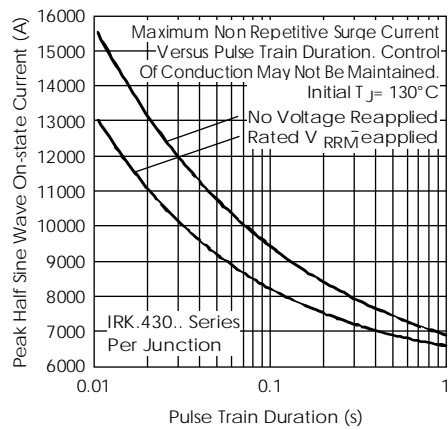


Fig. 6 - Maximum Non-Repetitive Surge Current

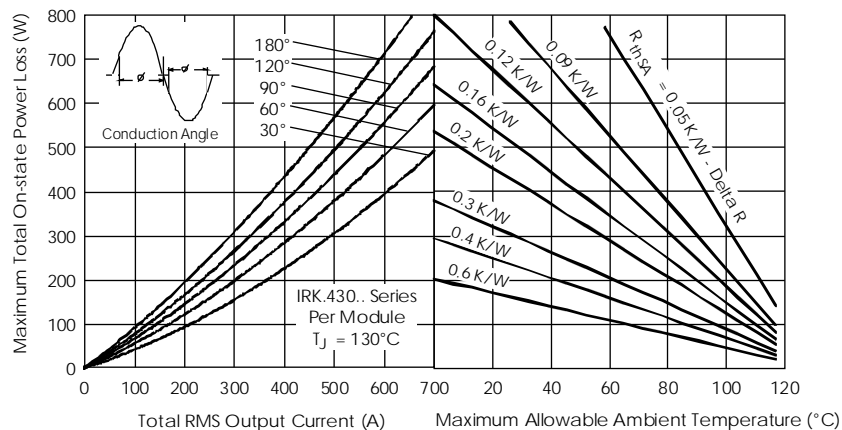


Fig. 7 - On-state Power Loss Characteristics

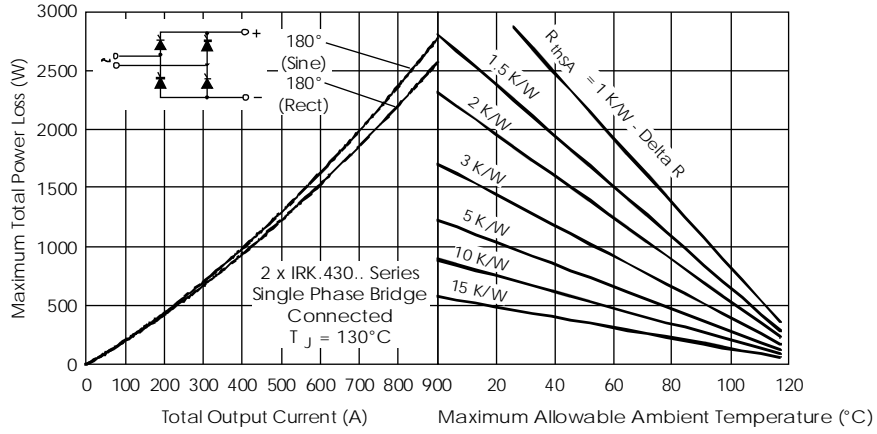


Fig. 8 - On-state Power Loss Characteristics

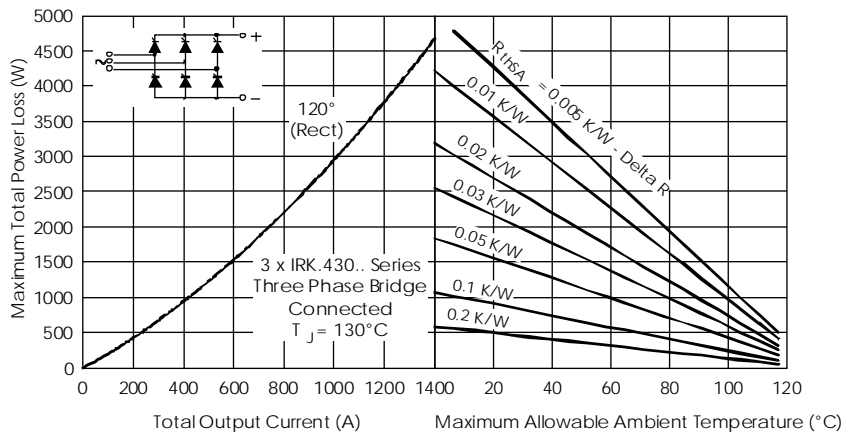


Fig. 9 - On-state Power Loss Characteristics

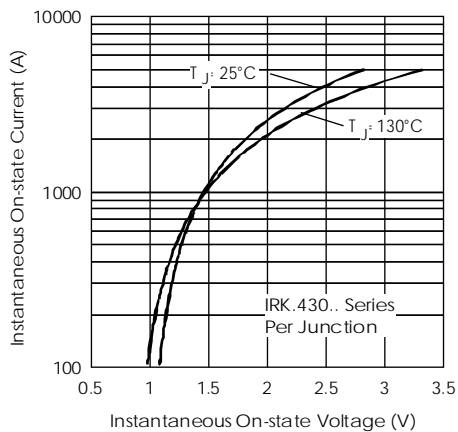


Fig. 10 - On-state Voltage Drop Characteristics

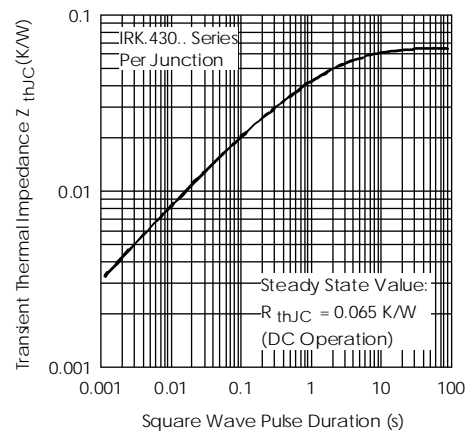


Fig. 11 - Thermal Impedance  $Z_{thJC}$  Characteristics

**IRK.430.. Series**

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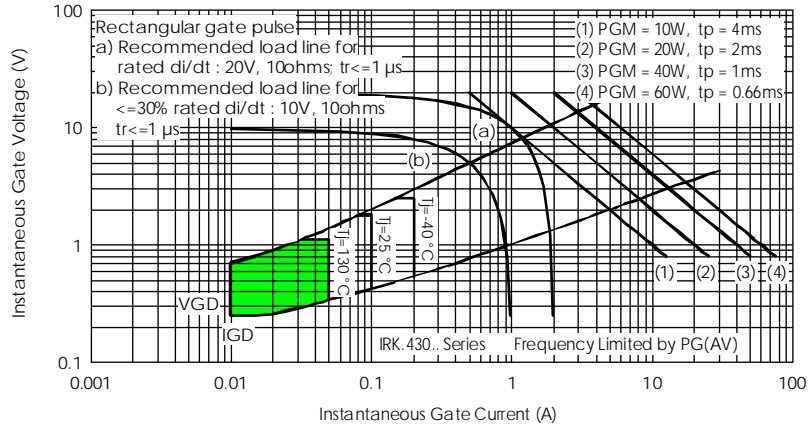


Fig. 12 - Gate Characteristics